

Heterostructure of two different 2D materials based on MoS₂ nanoflowers@rGO: an electrode material for sodium-ion capacitor

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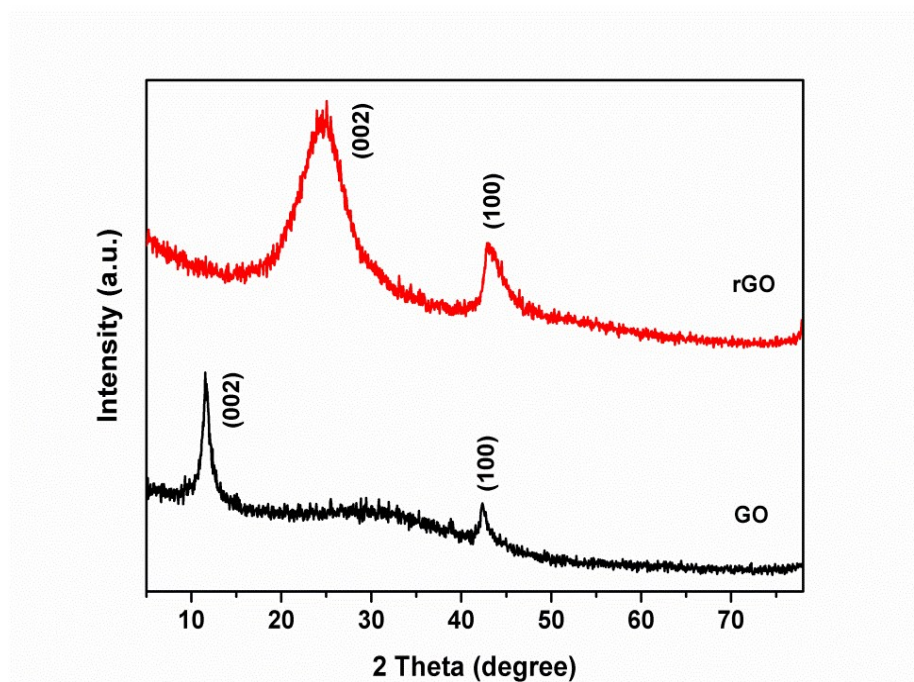


Fig. S1 XRD pattern of GO and rGO

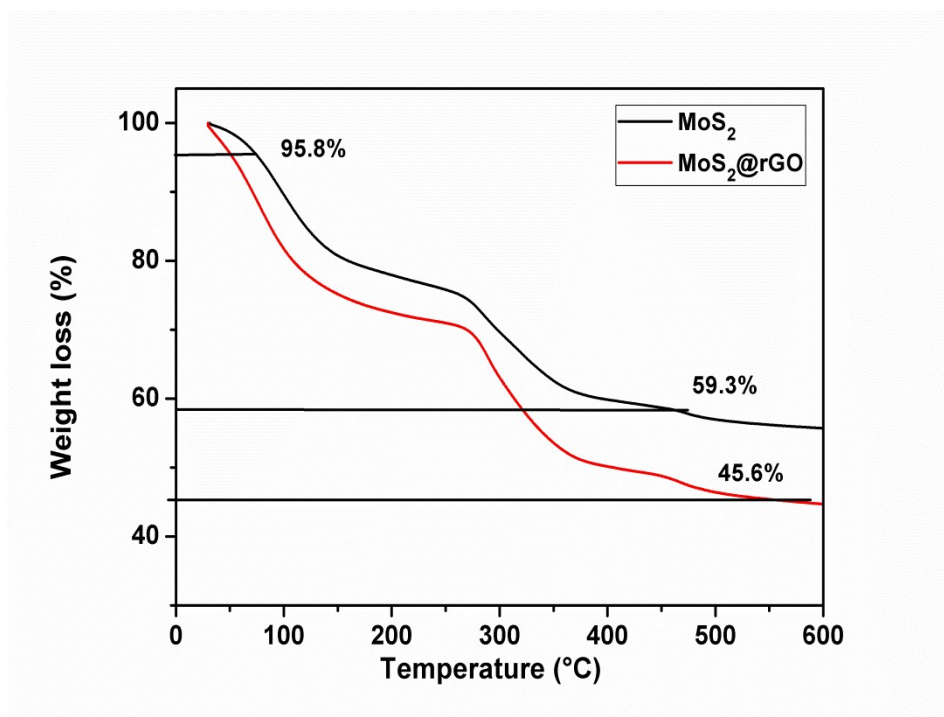


Fig. S2 TG curve of MoS₂ and MoS₂@rGO composite

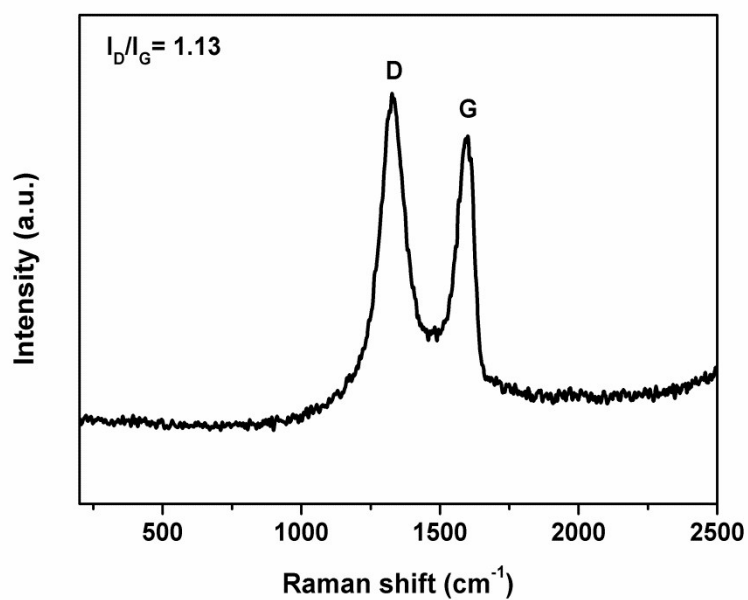


Fig. S3 Raman spectrum of rGO

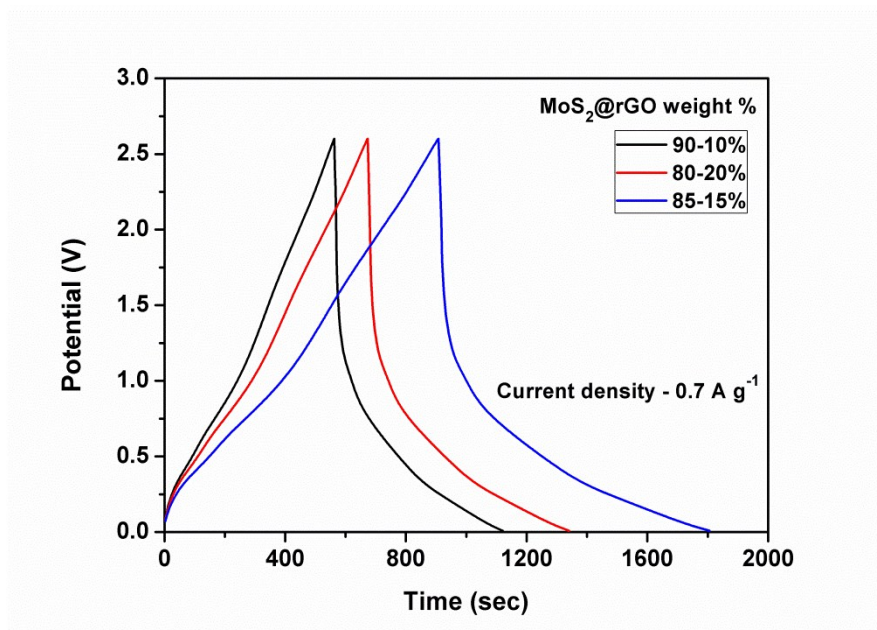


Fig. S4 Galvanostatic charge-discharge curves of MoS₂@rGO composites with different weight percentage

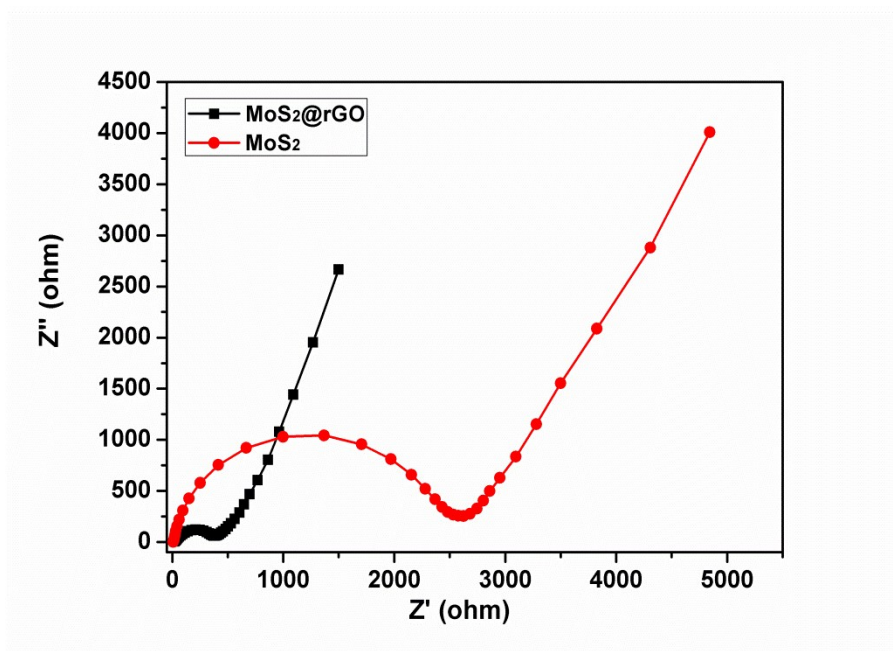


Fig. S5 Nyquist plot of MoS₂ and MoS₂@rGO composite

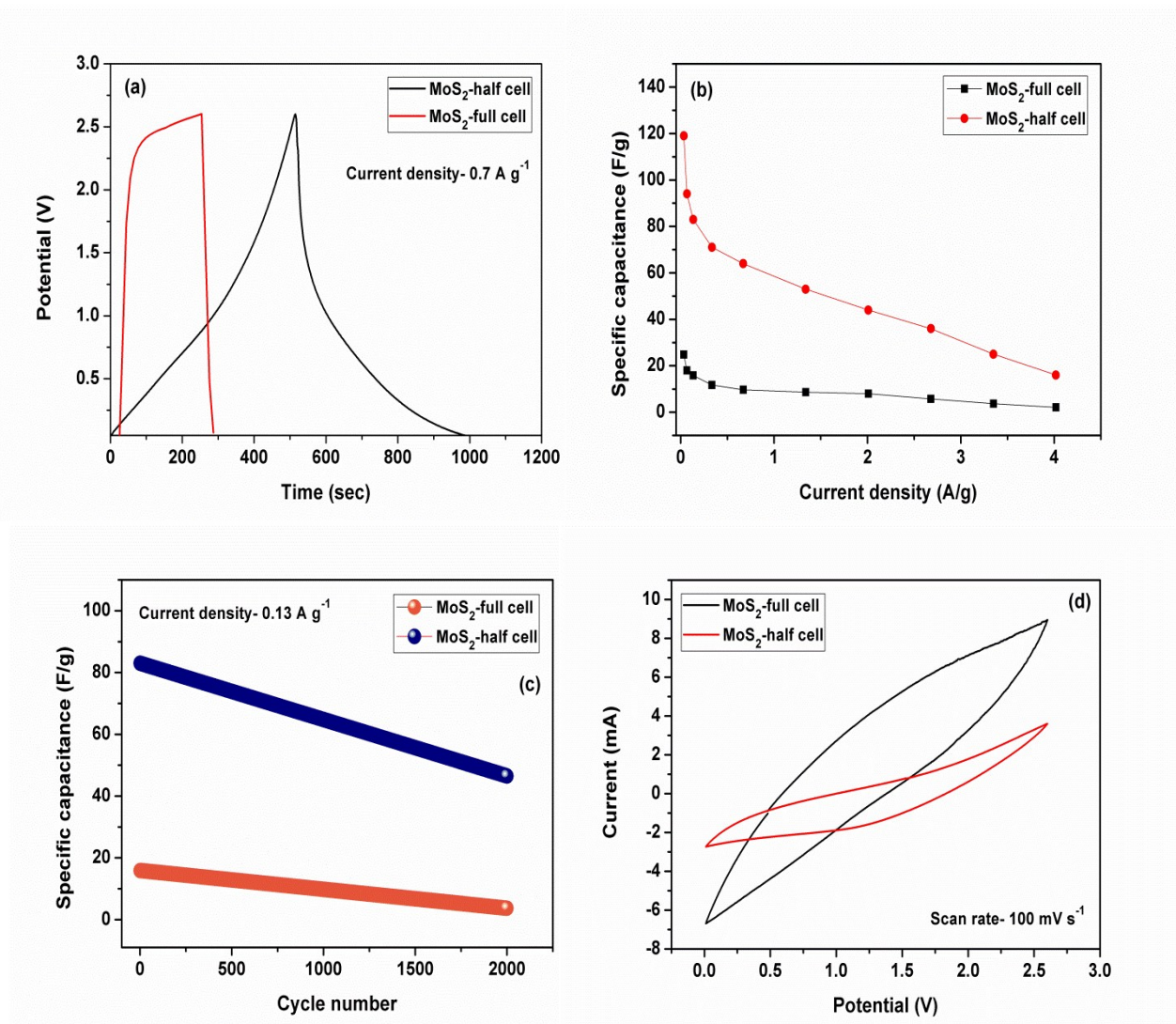


Fig. S6 Electrochemical performance of pristine MoS₂ vs Na/Na⁺ (half cell & full cell). (a) Galvanostatic charge-discharge curves (b) Specific capacitances at different current densities (c) Cycling stability (d) Cyclic voltammograms at different scan rate

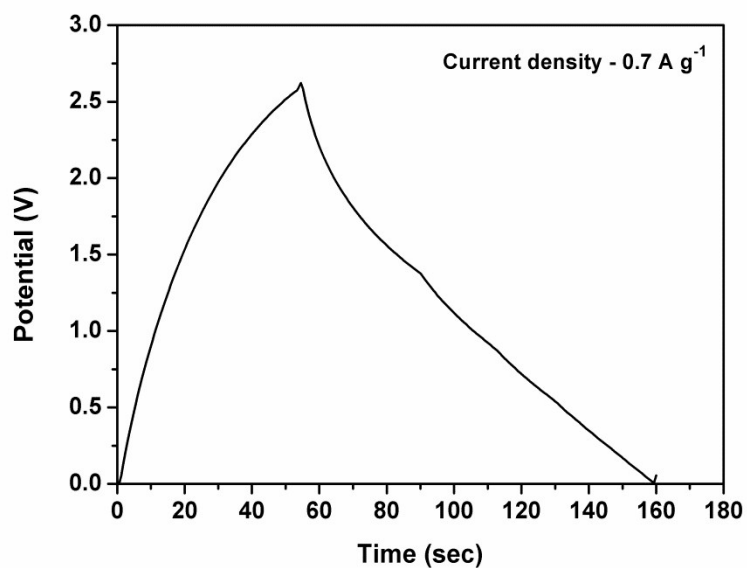


Fig. S7 Galvanostatic charge-discharge curve of rGO (full cell)

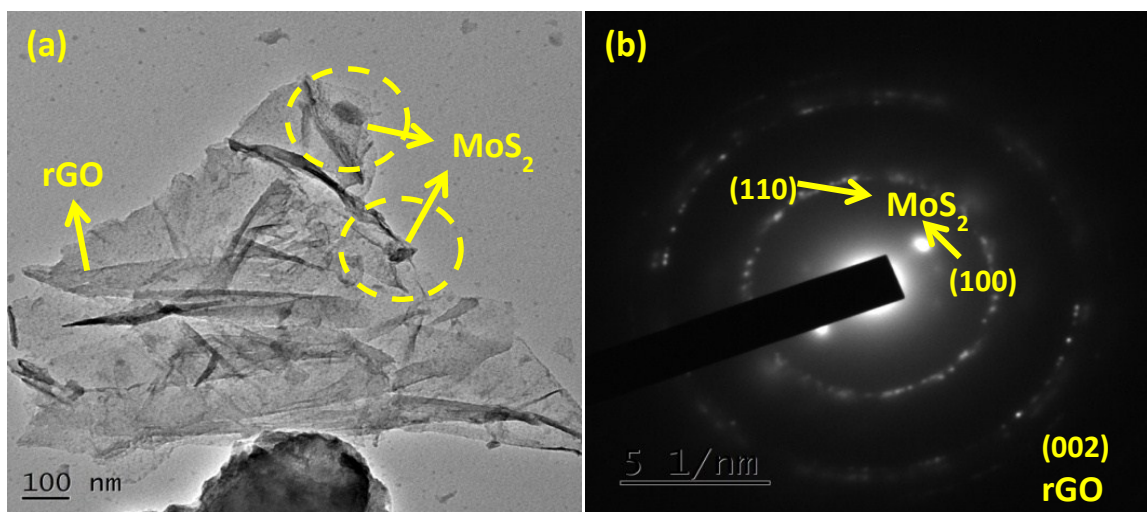


Fig. S8 (a) HRTEM image and (b) SAED pattern of MoS₂@rGO composite electrode after 2000 cycles

Table. S1 Comparison of specific capacitance of MoS₂ based electrode materials for super capacitor application in aqueous and non-aqueous electrolytes

S.No	Material	Method	Electrolyte	Scan rate/ Current density	Specific capacitance (Fg ⁻¹)	Reference
1.	MoS ₂	CBD	0.5 M Na ₂ SO ₄	5 mVs ⁻¹	576	37
2.	MoS ₂	Hydrothermal	1 M Na ₂ SO ₄ 1 M KCl	1 mVs ⁻¹ 1 mVs ⁻¹	376 403	38
3.	MoS ₂	Hydrothermal	1 M Na ₂ SO ₄	5 mVs ⁻¹	122	39
4.	MoS ₂	CVD	0.5 M H ₂ SO ₄	1 mVs ⁻¹	100	40
5.	MoS ₂ /graphene composite	Hydrothermal	1 M NaClO ₄ (in PC+FEC)	1.5 C (C rate)	50 (full cell)	28
6.	MoS ₂	Solid-gas reaction method	1 M NaClO ₄ (in PC)	1 mVs ⁻¹	118 mAhg ⁻¹ specific capacity, (half cell)	27
7.	MoS ₂ @rGO composite	Hydrothermal	0.75 M NaPF ₆ (in EC+DEC)	0.03 Ag ⁻¹	226, (half cell) 55 (full cell)	Present work